HUASHUO
SEMICONDUCTOR

HSM24P03

P-Ch 30V Fast Switching MOSFETs

Description

The HSM24P03 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

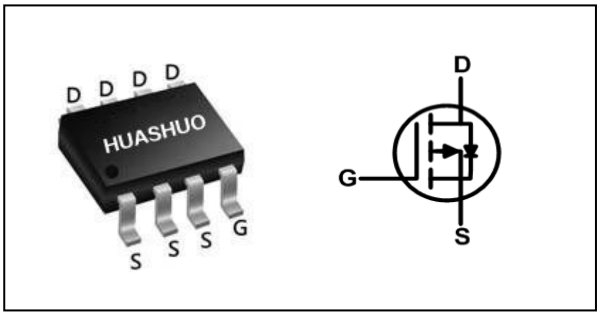
The HSM24P03 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-30	V
$R_{DS(ON),typ}$	3.8	mΩ
I_D	-24	A

SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ -10V[1]	-24	A
I_D@T_C=100˚C	Continuous Drain Current, V_{GS} @ -10V[1]	-	A
I_{DM}	Pulsed Drain Current[2]	-96	A
P_D@T_A=25˚C	Total Power Dissipation[4]	2.1	W
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1](t≦10S)	---	-	˚C/W
	Thermal Resistance Junction-ambient [1](Steady State)	---	60	˚C/W
$R_{\theta JC}$	Thermal Resistance Junction-case [1]	---	24	˚C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-17A	---	3.8	4.8	mΩ
		V_{GS}=-4.5V , I_D=-10A	---	5.8	7.8	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.2	-1.6	-2.2	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55℃	---	---	-10	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
Q_g	Total Gate Charge (-10V)	V_{DS}=-15V , V_{GS}=-10V , I_D=-10A	---	110	---	nC
Q_{gs}	Gate-Source Charge		---	15	---	
Q_{gd}	Gate-Drain Charge		---	18	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=6Ω, I_D=-1A	---	28	---	ns
T_r	Rise Time		---	17	---	
$T_{d(off)}$	Turn-Off Delay Time		---	180	---	
T_f	Fall Time		---	73	---	
C_{iss}	Input Capacitance	V_{DS}=-25V , V_{GS}=0V , f=1MHz	---	6240	---	pF
C_{oss}	Output Capacitance		---	780	---	
C_{rss}	Reverse Transfer Capacitance		---	410	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-24	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The power dissipation is limited by 150℃ junction temperature

4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

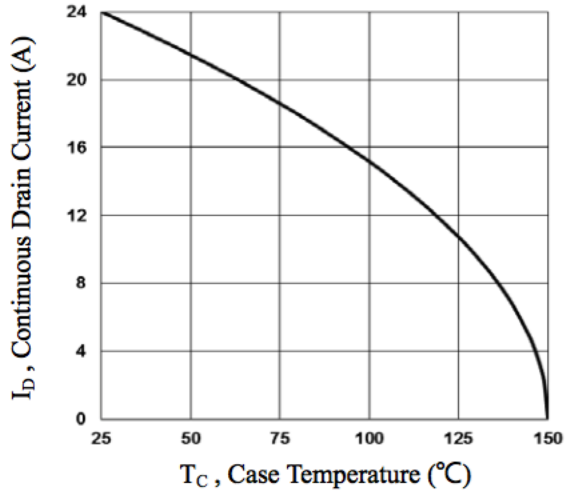


Fig.1 Continuous Drain Current vs. T_C

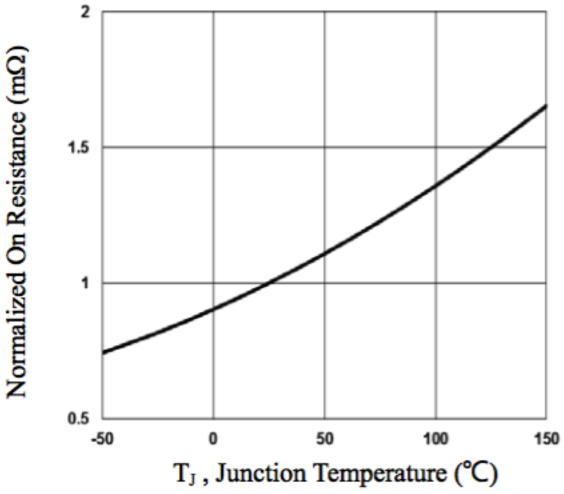


Fig.2 Normalized RDSON vs. T_J

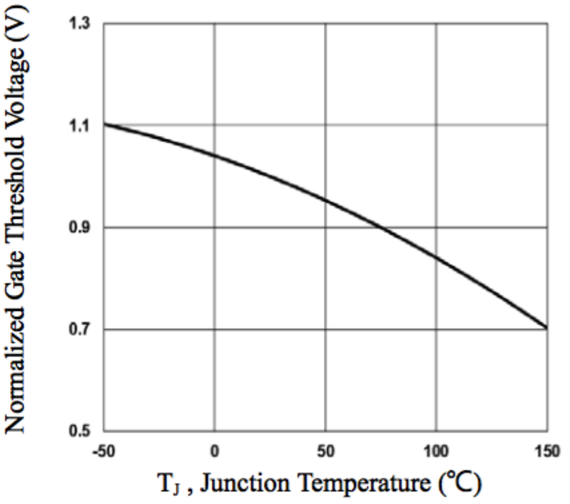


Fig.3 Normalized Vth vs. Tj

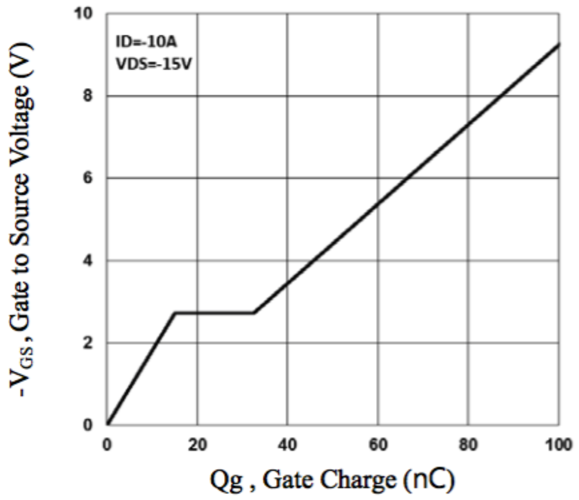


Fig.4 Gate Charge Waveform

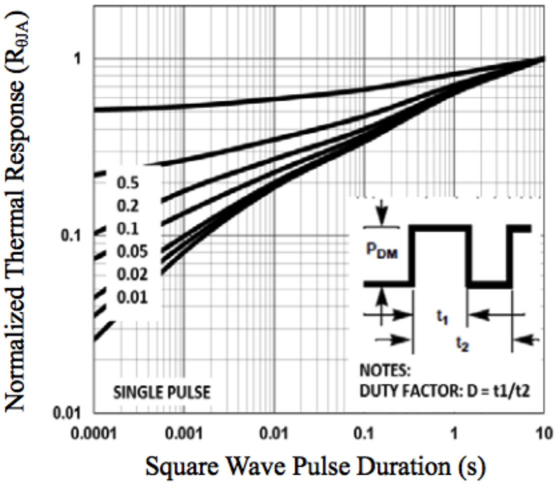


Fig.5 Normalized Transient Impedance

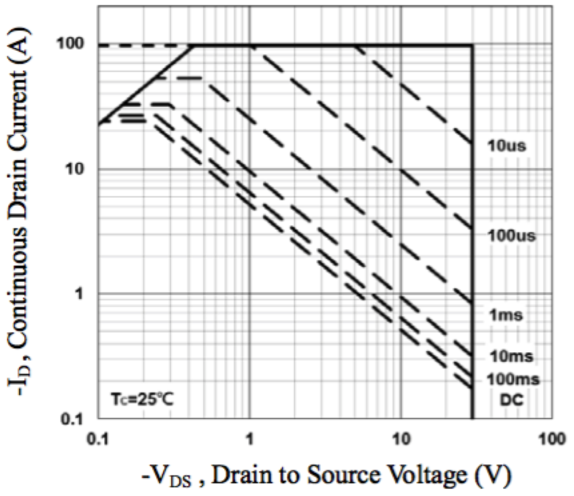


Fig.6 Maximum Safe Operation Area

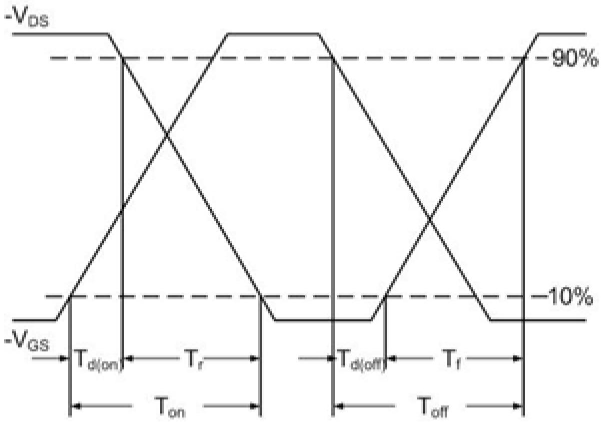


Fig.7 Switching Time Waveform

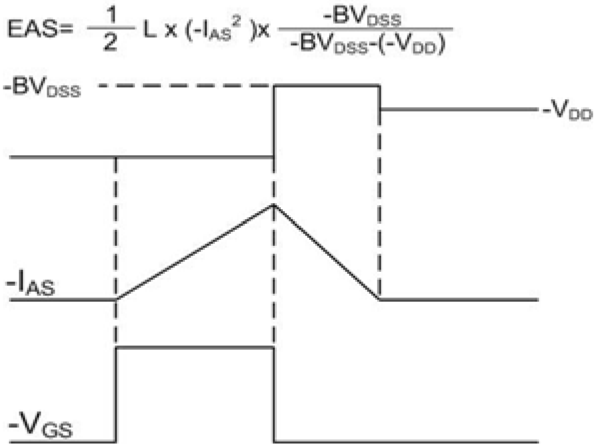
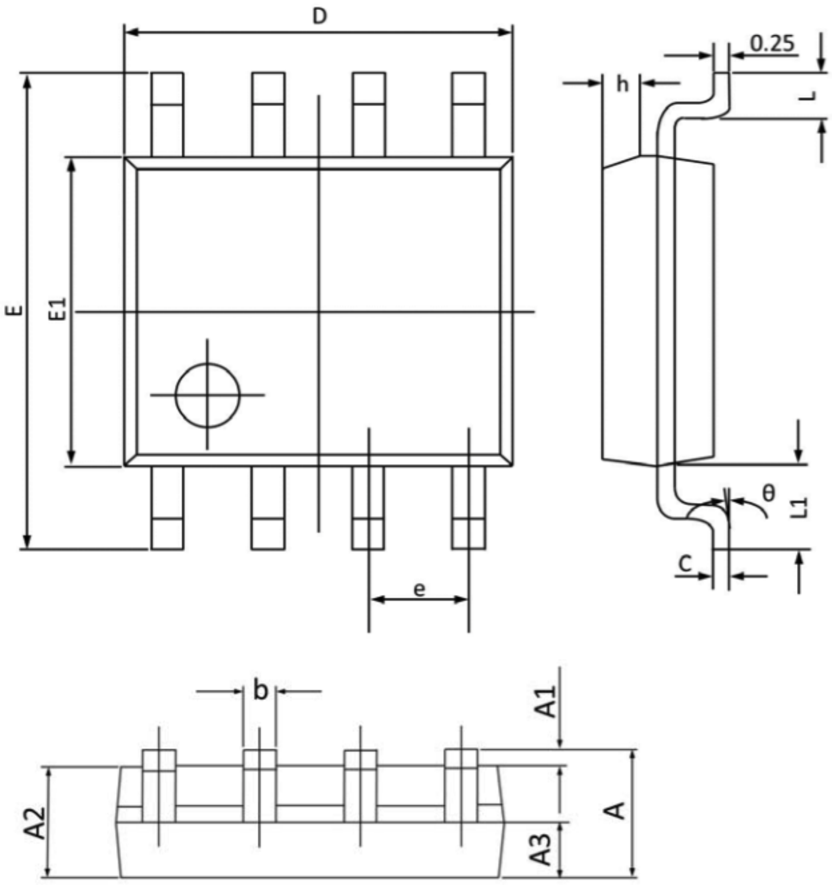


Fig.8 Unclamped Inductive Switching Waveform

SOP8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.068
A1	0.100	0.250	0.004	0.009
A2	1.300	1.500	0.052	0.059
A3	0.600	0.700	0.024	0.027
b	0.390	0.480	0.016	0.018
c	0.210	0.260	0.009	0.010
D	4.700	5.100	0.186	0.200
E	5.800	6.200	0.229	0.244
E1	3.700	4.100	0.146	0.161
e	1.270(BSC)		0.050(BSC)	
h	0.250	0.500	0.010	0.019
L	0.500	0.800	0.019	0.031
L1	1.050(BSC)		0.041(BSC)	
θ	0°	8°	0°	8°